

**FIG. 1**





1 μm  
Sintered GaN Fracture Surface  
File Name = S-GaN Fracture Surface Size.tif N = 2  
Noise Reduction = Prol. Avg.  
Aperture Size = 100.0 μm Date = 9 Oct 2004  
Mag = 5.00 KX EHT = 15.00 kV WD = 22 mm Spd Size = 240 Scan Speed = 11 Collector Bias = 300 V Chamber = 4.79e-001 Pa Detector = SEI Dong-Su Park

FIG. 3

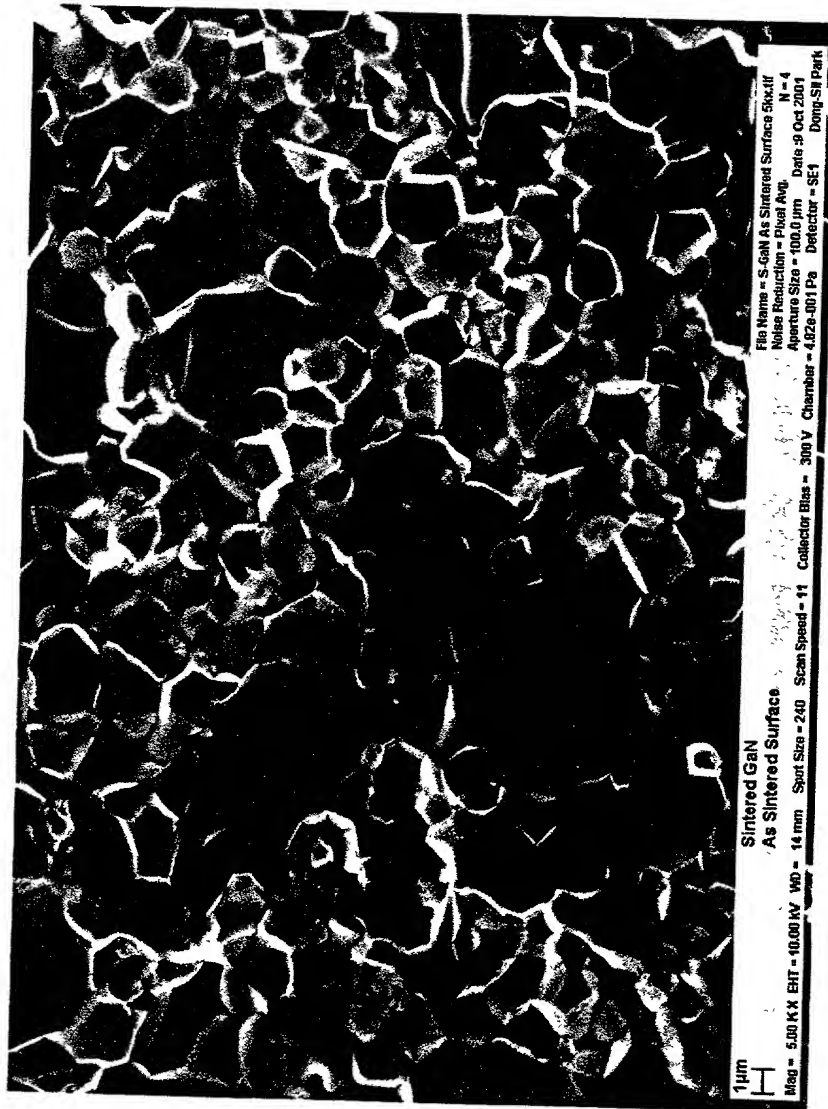


FIG. 4

Scanning electron micrograph (SEM) of a fractured surface. The image shows a complex, rough, and irregular fracture pattern with sharp edges and deep crevices. A scale bar in the bottom right corner indicates 100 μm. Technical data in the bottom right corner includes X282 magnification and 15kV voltage.



FIG. 5